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Giant edge spin accumulation in a symmetric quantum well with two subbands

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We have studied the edge spin accumulation in a high mobility two-dimensional electron gas formed in a symmetric well with two subbands. This study is strongly motivated by the recent experiment of Hernandez *et al.* [Phys. Rev. B **88**, 161305(R) (2013)] who demonstrated the spin accumulation near the edges of a bilayer symmetric GaAs structure in contrast to no effect in a single-layer configuration. The intrinsic mechanism of the spin-orbit interaction we consider arises from the coupling between two subband states of opposite parities. We obtain a parametrically large magnitude of the edge spin density for the two-subband sample as compared to the usual single-subband structure. We show that the presence of a gap in the system, i.e., the energy separation Δ between the two subband bottoms, changes drastically the picture of the edge spin accumulation. Thus one can easily proceed from the regime of weak spin accumulation to the regime of strong one by varying the Fermi energy (electron density) and/or Δ. We estimate that by changing the gap Δ from zero up to $1 \div 2$ K, the magnitude of the effect changes by three orders of magnitude. This opens up the possibility for the design of new spintronic devices.

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Spin currents and spin accumulation [1, 2] are topics of great current interest both experimentally and theoretically. These phenomena are due to the spin-orbit coupling and are important for the future of spin electronics [3]. There are two distinct spin-orbit mechanisms, the extrinsic one due to the Mott asymmetry in the electron scattering off impurities [4, 5], and the intrinsic one [6, 7] due to spin-orbit induced splitting of the electron spectrum. The latter has recently renewed the interest in this field, which has existed for quite a long time [4, 5, 8, 9]. The edge spin-density accumulation, related to either the Mott asymmetry by impurities [10] (2D electrons) or the intrinsic mechanism (2D holes) [11, 12], has been experimentally observed.

It is known [2, 13–15] that in the diffusive regime with a weak spin orbit interaction, i.e., when the spin diffusion length is much larger than the mean free path, the edge spin density is entirely due to the spin flux coming from the bulk. In contrast, the physics of the edge spin-density accumulation for the intrinsic mechanism in the opposite case of strong spin-orbit splitting [16] only recently has been understood [17–21]. This includes both the case of a ballistic structure in which the mean free path is the largest lengthscale in the problem, and the case of a diffusive sample but with large spin-orbit splitting of the spectrum so that the spin-precession length is smaller than the mean free path. This latter case we term the quasi-ballistic regime. In particular, it has been shown [21] that in this regime there is no direct relation between edge spin-density and bulk spin current. For example, in the case of 2D holes in the quasi-ballistic regime the edge spin-density, which is due to the spin current from the bulk, is parametrically smaller than the density generated upon the boundary scattering.

The experiment of Hernandez *et al.* [22] is interesting and intriguing in many aspects. It demonstrated the spin accumulation near the edges of a high mobility two-dimensional electron system in a bilayer symmetric GaAs structure in contrast to no effect in a single-layer configuration. The observed effect is quite big, i.e., it seems bigger than in the experiment by Kato *et al.* [10], where for a GaAs sample the result was explained by the extrinsic interaction with impurities. Note that the structure studied in [22] has inversion symmetry and therefore the usual Rashba term is absent. On the other hand, the linear-in-momentum Dresselhaus term is known not to lead to a spin current in the bulk. In addition, it cannot create a smooth, within the scale of the spin-precession length, edge spin density upon boundary scattering for any reasonably short-ranged impurity scattering in the bulk, as is shown in Ref. [21]. There is clearly a significant difference between the observed edge spin density in two-subband vs. the one-subband cases (i.e., strong edge accumulation effect vs no effect). This motivated us to look for the explanation of this phenomenon using the inter-subband Rashba-like Hamiltonian arising in two-subband wells [24],[25].

Here we follow the method proposed in [21] to calculate the edge spin density which appears due to boundary scattering [Fig. 1(a)] in the quasi-ballistic regime for a Rashba-like Hamiltonian with inter-subband coupling [24],[25] describing the two-subband well [Fig. 1(b)] in the experiment of Ref. [22]. In this quasi-ballistic regime the characteristic length of the spin accumulation near the boundary is smaller than the mean free path. In fact, the mean free path in the experiment is around 30 μm [22], which indeed exceeds all the characteristic lengths of our theory. We believe that we have explained the experimental results, in particular, the large magnitude of the edge spin density for the two-subband sample compared

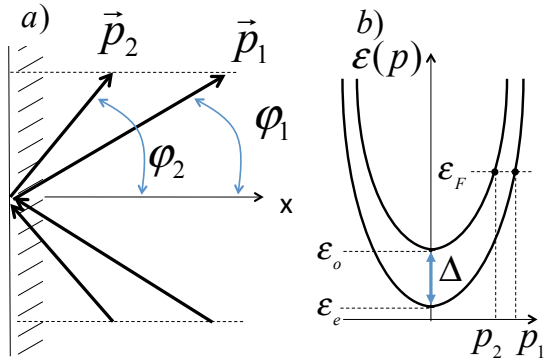

Figure 1. Schematics of the boundary specular scattering in the presence of spin-orbit coupling. Plus and minus modes are shown for the same energy and the same wave vectors along the boundary.

to the usual single-band structure with either the Rashba or Dresselhaus interactions.

Interestingly, we have found that the presence of the gap Δ between two sub-band edges [Fig. 1(b)] drastically changes the scenario of the edge spin accumulation, so that the physics is now determined by the value of the parameter $\xi = 2\eta k_F/\Delta \equiv L_\Delta/L_s$ [Fig. 2], where $L_\Delta = \hbar v_F/\Delta$, $L_s = \hbar^2/2m\eta$ are the 'coherence" and the spin-precession lengths. Here $p_F = \hbar k_F = m v_F$ is the Fermi momentum, η is the inter-subband spin-orbit coupling constant. The parameter ξ can have an arbitrary value even for a small η since the gap Δ can be made much smaller than the Fermi energy. Thus one can easily go from the regime of weak spin accumulation (large $\xi \gg 1$) over to the regime of strong spin accumulation (ξ is order of unity) just by slight increase of the gap value. As we discuss later, for GaAs structure similar to that used in Ref. [22], it is enough to change the gap Δ from zero up to $1 \div 2$ K only in order to increase the magnitude of the effect by the three orders.

Therefore despite the problem in question resembling very much the usual Rashba problem (there are two copies of them because each state is doubly degenerate), the presence of the gap changes physics of the edge spin accumulation completely. The most pronounced change happens at $L_\Delta \simeq 0.5 L_s$, where the edge spin density $S_z(x)$ is maximized and its order of magnitude is given by k_E/L_s [Fig. 2], which is parametrically larger than in the single-band case. Here $k_E = eE\tau_{tr}/\hbar$, e is the modulus of the electron charge, E is the magnitude of the in-plane (driving) electric field [22] and τ_{tr} is the transport scattering time due to the impurities in the bulk of a sample.

We consider specular scattering (i.e., a straight boundary for simplicity, Fig. 1(a)) and a Fermi energy much larger than the gap Δ between the subbands, i.e., $\varepsilon_F \gg \Delta$. In this regime the two subbands are occupied, which corresponds to the conditions of experiment [23]. Moreover, the spin-orbit interaction is weak and therefore "coherent" and spin-precession length scales are large compared to the Fermi wave length, $L_\Delta, L_s \gg \lambda_F$. Our calculation shows that the characteristic spatial scale of the edge spin density is $\Lambda = L_\Delta L_s/\sqrt{L_\Delta^2 + L_s^2}$.

Model Hamiltonian. — The Hamiltonian of a symmetric quantum well with two subbands and intersubband-induced SO interaction resembles that of the ordinary Rashba model. In contrast to the latter, the intersubband SO interaction is nonzero even in symmetric structures. As derived in Refs.[24, 25], the 4×4 Hamiltonian describing a (symmetric) two-subband well is

$$H = (\frac{p^2}{2m} + \varepsilon_+)1 \otimes 1 - \varepsilon_- \tau_z \otimes 1 + (\eta/\hbar)\tau_x \otimes (p_x\sigma_y - p_y\sigma_x), \quad (1)$$

where m is the effective mass, $\varepsilon_\pm = (\varepsilon_o \pm \varepsilon_e)/2$, ε_e and ε_o are quantized energies of the lowest (even) and first excited (odd) subbands, respectively, measured from the bottom of the quantum well, $\tau_{x,y,z}$ denote the Pauli matrices describing the subband (or pseudospin) degree of freedom, and $\sigma_{x,y,z}$ are Pauli matrices referring to the electron spin. The inter-subband SO coupling η is expressed [24] in terms of the gradients of the Hartree-type contribution to the electron potential, the external gate and doping potentials, and the structural quantum-well potential profile. Note that the gap is $\Delta = \varepsilon_o - \varepsilon_e = 2\varepsilon_-$.

Theoretical approach. To calculate the edge spin density in the quasi-ballistic regime we follow the method developed in Refs. [20, 21] for the case of the single-subband Rashba Hamiltonian. Assuming that the spatial scale of the edge spin accumulation (Λ) is much smaller than the mean free path (l) (quasi-ballistic regime), we solve the edge spin problem by the method of scattering states, i.e., we find the exact quantum mechanical solution of the electron scattering by an impenetrable straight boundary [Fig. 1(a)] at a given Fermi energy. These solutions are then used in the calculation of the (mean) spin density profile. Depending on the Fermi level location some of the involved states can be evanescent modes. This happens, for example, when the Fermi level is within the gap between the two subbands ($\varepsilon_e < \varepsilon_F < \varepsilon_o$), i.e., only one subband is occupied. The populations of the incoming states are found from the solution of the kinetic equation for the spin-density matrix in the bulk (2D) of the sample in the presence of electric field [27]. These distribution functions are used as the input parameters for the part of the problem related to the scattering by the straight boundary. Besides the quasi-ballistic regime ($\Lambda \ll l$), we assume that the Fermi energy ε_F is much larger than the gap, $\varepsilon_F \gg \Delta$, i.e., both sub-bands are occupied. We also consider the SO interaction weak so that $\eta k_F \ll \varepsilon_F \Rightarrow L_\Delta, L_s \gg \lambda_F = 2\pi/k_F$. The ratio L_Δ/L_s can be arbitrary.

The Hamiltonian (1) has 4 eigensolutions $\Psi_{i,s}$,

$\Psi_{1,\uparrow}$, $\Psi_{1,\downarrow}$, $\Psi_{2,\uparrow}$, $\Psi_{2,\downarrow}$ with the corresponding energy spectrum

$$\varepsilon_{1,2}(p) = \frac{p^2}{2m} + \varepsilon_+ \mp \sqrt{\varepsilon_-^2 + \eta^2 p^2/\hbar^2}, \tag{2}$$

where the subscript $i = 1, 2$ corresponds to the lower (higher) in energy sub-band. Each sub-band is doubly degenerate with respect to the "spin direction" $s = \uparrow, \downarrow$ (Kramers pairs). Upon scattering by the straight boundary where energy and momentum p_y along the boundary are conserved, the states in the pair $\Psi_{1,\uparrow}(\varphi_1, \theta_1), \Psi_{2,\downarrow}(\varphi_2, \theta_2)$ mix up and form two *scattering* states, Eqs. (3),(4) [similarly for the pair $\Psi_{1,\downarrow}(\varphi_1, \theta_1), \Psi_{2,\uparrow}(\varphi_2, \theta_2)$]. For this pair of scattering states, we have for the scattering by the hard wall located at $x = 0$ [Fig. 1(a)]

$$\tilde{\Psi}_{1,\uparrow}(x,y)|_{x=0} = e^{ik_y y}[\Psi_{1,\uparrow}(\pi - \varphi_1, \theta_1)e^{-ik_1 x} + F_{1,\uparrow}^{1,\uparrow}\Psi_{1,\uparrow}(\varphi_1, \theta_1)e^{ik_1 x} + F_{1,\uparrow}^{2,\downarrow}\Psi_{2,\downarrow}(\varphi_2, \theta_2)e^{ik_2 x}]|_{x=0} = 0, \tag{3}$$

$$\tilde{\Psi}_{2,\downarrow}(x,y)|_{x=0} = e^{ik_y y}[\Psi_{2,\downarrow}(\pi - \varphi_2, \theta_2)e^{-ik_2 x} + F_{2,\downarrow}^{1,\uparrow}\Psi_{1,\uparrow}(\varphi_1, \theta_1)e^{ik_1 x} + F_{2,\downarrow}^{2,\downarrow}\Psi_{2,\downarrow}(\varphi_2, \theta_2)e^{ik_2 x}]|_{x=0} = 0, \tag{4}$$

with $p_1^2 = \hbar^2(k_y^2 + k_1^2)$, $p_2^2 = \hbar^2(k_y^2 + k_2^2)$, $\varepsilon_1(p_1) = \varepsilon_2(p_2) = \varepsilon$. The momenta p_1, p_2 describe states belonging to subbands 1 and 2 for a given energy ε, see Fig. 1(b). The angles φ_1, φ_2 (between the corresponding momenta and the positive direction of the x-axis) are expressed as $\sin(\varphi_1) = \hbar k_y/p_1$ and $\sin(\varphi_2) = \hbar k_y/p_2$. The angles θ_1, θ_2 are defined via $\cos\theta_{1,2} = 1/\sqrt{1 + (\eta p_{1,2}/\hbar\varepsilon_-)^2}$.

From the above equations we can find the components of the unitary scattering matrix $\hat{S}$

$$S_{1,\uparrow}^{1,\uparrow} = F_{1,\uparrow}^{1,\uparrow},\ S_{2,\downarrow}^{2,\downarrow} = F_{2,\downarrow}^{2,\downarrow},\ S_{1,\uparrow}^{2,\downarrow} = S_{2,\downarrow}^{1,\uparrow} = F_{1,\uparrow}^{2,\downarrow}\sqrt{\frac{v_{x,2}}{v_{x,1}}}, \tag{5}$$

where the group velocities in the subbands $i = 1, 2$ are $v_{x,i} = \partial\varepsilon_i/\partial p_x$ and the scattering amplitudes are

$$\begin{aligned} F_{1,\uparrow}^{1,\uparrow} &= [e^{-i\varphi_1}\sin(\theta_1/2)\sin(\theta_2/2) - e^{i\varphi_2}\cos(\theta_1/2)\cos(\theta_2/2)]/D;\ \ F_{1,\uparrow}^{2,\downarrow} = -\sin\theta_1\cos\varphi_1/D, \\ F_{2,\downarrow}^{2,\downarrow} &= -[e^{i\varphi_1}\sin(\theta_1/2)\sin(\theta_2/2) - e^{-i\varphi_2}\cos(\theta_1/2)\cos(\theta_2/2)]/D;\ \ F_{2,\downarrow}^{1,\uparrow} = -\sin\theta_2\cos\varphi_2/D, \\ D &= e^{i\varphi_2}\cos(\theta_1/2)\cos(\theta_2/2) + e^{i\varphi_1}\sin(\theta_1/2)\sin(\theta_2/2). \end{aligned} \tag{6}$$

Similar equations can be written for the pair $\Psi_{1,\downarrow}(\varphi_1), \Psi_{2,\uparrow}(\varphi_2)$, and the corresponding scattering matrix elements $S_{1,\downarrow}^{1,\downarrow}$, $S_{2,\uparrow}^{2,\uparrow}$, $S_{1,\downarrow}^{2,\uparrow} = S_{2,\uparrow}^{1,\downarrow}$ can be determined.

The expectation value of the z component of the spin as a function of coordinates is given by the following expression:

$$\langle S_z(x)\rangle = \sum_{i,s}\int \frac{dk_y}{(2\pi)^2}\frac{d\varepsilon}{v_{x,i}} f_i(\varepsilon, k_y) \times\langle\tilde{\Psi}_{i,s}(x)|\hat{S}_z|\tilde{\Psi}_{i,s}(x)\rangle \tag{7}$$

Here $f_i(\varepsilon, k_y)$ is the distribution function of the electron state in the sub-band i for a given energy and given wave vector k_y along the boundary. Then we can calculate the most important part of the spin density which is smooth on the scale of the Fermi wave length [26] and involves the interference of the outgoing waves (two last terms in Eqs. (3) and (4))

$$\langle S_z(x)\rangle = \mathrm{Re}\left\{\int \frac{dk_y}{(2\pi)^2}\frac{d\varepsilon}{\sqrt{v_{x,1}v_{x,2}}}\left[S_{2,\uparrow}^{2,\uparrow}\cdot(S_{2,\uparrow}^{1,\downarrow})^\star\cdot\langle\Psi_{1,\downarrow}(\varphi_1)|\hat{\sigma}_z|\Psi_{2,\uparrow}(\varphi_2)\rangle + (\uparrow\leftrightarrows\downarrow)\right] \times e^{i(k_1-k_2)x}[f_1(\varepsilon, k_y) - f_2(\varepsilon, k_y)]\right\}. \tag{8}$$

Using the expressions above we obtain

$$\langle S_z(x)\rangle = -\Big\{ \int \frac{dk_y}{(2\pi)^2}\frac{d\varepsilon}{\sqrt{v_1 v_2}}\left[k_y \frac{\sqrt{\sin\theta_1 \sin\theta_2}(p_1^{-1}\cdot\sin\theta_1 + p_2^{-1}\cdot\sin\theta_2)}{\cos^2[(\theta_1-\theta_2)/2] - \sin\theta_1\sin\theta_2\sin^2[(\varphi_1-\varphi_2)/2]}\right] \times \sin[(p_1\cos\varphi_1 - p_2\cos\varphi_2)x/\hbar]\cdot[f_1(\varepsilon,k_y) - f_2(\varepsilon,k_y)]\Big\}. \quad (9)$$

We can calculate the edge spin density for arbitrary values of the parameter $\xi = L_\Delta/L_s$ using that $p_1 - p_2 \ll p_F$, i.e. the energy separation between two sub-bands $\sqrt{\Delta^2 + 4\eta^2 k_F^2}$ is much smaller than the Fermi energy. This means that $\theta_1 - \theta_2 \ll \theta_{1,2}$, and for the same reason $\varphi_2 - \varphi_1 \ll \varphi_{1,2}$. To proceed we need also the difference of the distribution functions entering Eq. (9). It can be calculated following the procedure described in Ref. [27]. We have done it assuming the set of inequalities $k_F^{-1} \ll d \ll L_s$, where d is the correlation radius of the impurity potential in the bulk of the structure. The first condition means that the scattering in the bulk is of the small-angle type. Both conditions are fulfilled for a high mobility GaAs structure. After presenting the general formula below, we will illustrate the calculation for the case of a weak spin-orbit coupling, $L_s \gg L_\Delta$. The final result derived from Eq. (9) reads

$$\langle S_z(x)\rangle = \frac{3k_E}{L_s}\Phi(\xi)J(x/\Lambda);\quad \Phi(\xi) = \frac{\xi}{(2\xi^2+1)\sqrt{\xi^2+1}}. \quad (10)$$

with the spatial dependence given by the integral

$$J(\frac{x}{\Lambda}) = \int_0^1 \frac{dz z^2}{\pi^2}\sin(\frac{x}{\Lambda\sqrt{1-z^2}}),\ \Lambda = \frac{L_\Delta L_s}{\sqrt{L_\Delta^2 + L_s^2}} \quad (11)$$

For $x \ll \Lambda$ we have $J(x) \propto x/\Lambda$. In opposite limit $x \gg \Lambda$, we obtain $J(x) \propto (\Lambda/x)^{3/2}\cos[(x/\Lambda) + \pi/4]$.

We see that the physical picture of the edge spin accumulation is totally different as compared to the case of usual Rashba system with one sub-band. We recall that in the latter the edge spin density is strongly suppressed as compared to the value k_E/L_s for any reasonably short-ranged impurity scattering in the bulk [21]. The suppression factor is $d^2/L_s^2 \ll 1$. It is very interesting that in the case $L_\Delta \lesssim L_s$ such a suppression does not occur. The reason for this is the presence of the gap Δ in the spectrum.

Weak spin-orbit coupling: $L_s \gg L_\Delta$. In this case we can calculate the difference of the distribution functions entering Eq. (9) using their expressions at $\eta = 0$, i.e.,

$$f_{1,2} = (eE\hbar k_y/m)\tau_{tr}(p_{1,2})\partial f_0/\partial\varepsilon, \quad (12)$$

where f_0 is the Fermi function, the electric field E is directed along the y-axis, and $\tau_{tr}(p)$ is the momentum-dependent transport scattering time calculated within the Born approximation due to impurity scattering in the bulk. The values of p_1, p_2 are related through

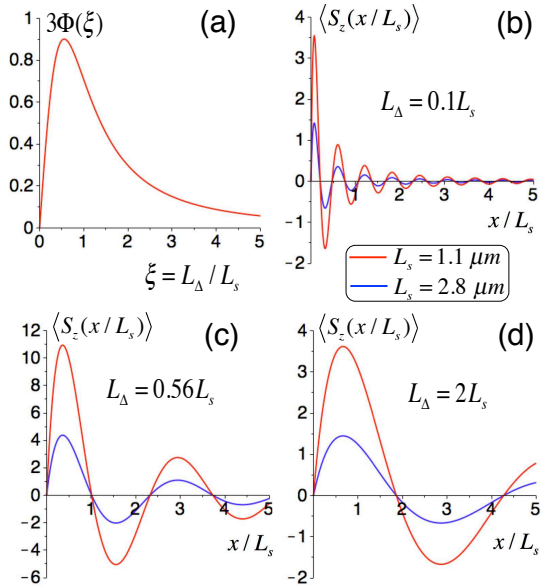

Figure 2. $\Phi(\xi)$ vs. ξ a) and the edge spin density $\langle S_z(x)\rangle$ in units of $10^6 cm^{-2}$ for distinct ratios L_Δ/L_s and two different values of L_s b)-c), as a function of x/L_s. Note that $\Phi(\xi)$ has a maximum at $\xi \sim 0.56 = L_\Delta/L_s$. This non-monotonic behavior is reflected in the overall amplitude of $\langle S_z(x)\rangle$, which is maximized for $L_\Delta = 0.56L_s$ c) and is suppressed as ξ deviates from this value b), d). Note that the amplitude of the oscillations is reduced as L_s increase (cf. blue and red curves in b)-d).)

$\varepsilon_1(p_1) = \varepsilon_2(p_2) = \varepsilon = \varepsilon_F$, Fig. 1(b). Using the condition $k_F d \gg 1$ (small-angle scattering in bulk), we obtain $(\tau_{tr}(p_1) - \tau_{tr}(p_2))/\tau_{tr} \approx 3(p_1 - p_2)/p_F \approx (3/(k_F L_\Delta)$. [28] We note that compared to the usual Rashba one-band case the difference of the distribution functions considered here is finite at $\eta = 0$, and is of the first order in $p_1 - p_2 = \hbar/L_\Delta$. In the one-band case the difference of the distribution functions is of the third order with respect to $p_1 - p_2 = \hbar/L_s$ (see Ref. 21). With increasing the gap value (Δ) from zero, the inter-subband spin-orbit interaction decreases and the inter-subband transion rates are suppressed in the collision integral due to impurities compared to the intra-subband ones. This leads to the lack of complete cancellation which occurs in the pure Rashba model (see Eqs. (14-16) in [21]) and recovering of the first order effect in $p_1 - p_2$. This is true for an arbitrary value of ξ. As for the considered case of the

weak SO coupling, the additional smallness comes in via the $\sin^2\theta \approx L_\Delta^2/L_s^2 \ll 1$ factor in Eq. (9) , and finally we obtain

$$\langle S_z(x)\rangle = 3k_E\frac{L_\Delta}{L_s^2}J(x/\Lambda). \quad (13)$$

The calculated edge spin density Eq. (10) is maximal at $L_\Delta \approx L_s$ when it is of the order of k_E/L_s. In the opposite limit $L_s \ll L_\Delta$, when with increasing SO coupling the spectrum approaches the usual Rashba type, $\langle S_z(x)\rangle$ decreases in magnitude as $k_E L_s/L_\Delta^2$ (see Fig. 2), finally approaching the limit calculated in Ref. 21 given by $\simeq (k_E/L_s)(d^2/L_s^2)$. The characteristic scale of the edge spin density variation in space is L_s. Thus for a given strength of the SO interaction, the magnitude of the edge spin density has non-monotonic dependence as a function of the L_Δ (or Δ), Fig.2. We note that if one takes the absolutely realistic value for the ratio $d/L_s = 0.1$, then the edge spin density obtained in Ref. [21] for the usual Rashba system with one sub-band equals in magnitude the density which follows from Eq. 10 at $\xi \approx 35$, where the latter is three orders of magnitude smaller than its maximal value at $\xi = 0.56$.

Comparison with the experiment. The experimental estimate of L_Δ is $\approx 1.4\times10^{-5}$ cm. For L_s we take two characteristic lengths $1.1\mu m$ and $2.8\mu m$. Note that the corresponding values of η are consistent with the ones obtained from the theoretical calculations [29] for structures similar to that used in the experiment of Ref. [22]. Thus the value $\xi = 0.1$ will reasonably correspond the above chosen lengths. Calculating τ_{tr} from the mobility $1.9\times10^6 cm^2/\mathrm{Vs}$, and using $E = 0.05$ mV/μm for the electric field in the quasi-ballistic region of the sample (both the mobility and E are taken from Ref. [22]), we plot $\langle S_z(x)\rangle$, see Fig. 2(b). The exact experimental value of the edge spin density is not known; the authors of Ref. [22] have estimated the threshold minimal value compatible with their observation as $3\times10^6 cm^{-2}$. Hence this number is consistent quite well with our calculations. We stress that the procedure just described, i.e. comparison of our theoretical predictions for the edge spin density with the experimental value of this quantity allows one to extract the value of η.

In conclusion, using a Rashba-like SO interaction arising from the coupling between two sub-band states of opposite parities in a symmetric two-subband quantum well, we have explained the main result of the experiment of Ref. [22]. In particular, we have explained the great difference between the effect in a bilayer structure compared to the one in a single-layer configuration. We show that presence of the gap between two sub-bands changes drastically the picture of the edge spin accumulation. Thus, by varying the gap value one can easily proceed from the regime of strong spin accumulation to the regime of weak spin accumulation. This opens up the possibility for the design of new spintronic devices.

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